

# Fast Recovery Epitaxial Diode (FRED)

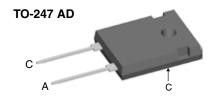
 V<sub>RSM</sub>
 V<sub>RRM</sub>
 Type

 V
 V

 600
 600
 DSEI 60-06A



 $I_{FAV} = 60 A$   $V_{RRM} = 600 V$  $t_{rr} = 35 ns$ 



A = Anode, C = Cathode

Symbol	Conditions			Maximum Rat	tings
I <sub>FRMS</sub>	T <sub>C</sub> = 70°C; rectangular, d = 0.5			100 60	A A
I <sub>FSM</sub>	$T_{VJ} = 45^{\circ}C;$		(50 Hz), sine (60 Hz), sine	550 600	A A
	$T_{VJ} = 150^{\circ}C;$		(50 Hz), sine (60 Hz), sine	480 520	A A
l²t	$T_{VJ} = 45^{\circ}C;$		(50 Hz), sine (60 Hz), sine	1510 1490	A <sup>2</sup> s A <sup>2</sup> s
	T <sub>VJ</sub> = 150°C;		(50 Hz), sine (60 Hz), sine	1150 1120	A <sup>2</sup> s A <sup>2</sup> s
T <sub>VJ</sub> T <sub>VJM</sub> T <sub>stg</sub>				-55+150 150 -55+150	O° O° O°
P <sub>tot</sub>	T <sub>C</sub> = 25°C			166	W
M <sub>d</sub>	mounting tord	que		0.81.2	Nm
Weight	typical			6	g

Symbol	Conditions	haracte	haracteristic Values		
		typ.	max.		
I <sub>R</sub>	$egin{array}{lll} V_{R} = V_{RRM} & T_{VJ} = 25^{\circ} C \\ V_{R} = 0.8 \cdot V_{RRM} & T_{VJ} = 25^{\circ} C \\ V_{R} = 0.8 \cdot V_{RRM} & T_{VJ} = 125^{\circ} C \\ \end{array}$		200 100 14	μA μA mA	
V <sub>F</sub>	$I_F = 70 \text{ A}$ $T_{VJ} = 150^{\circ}\text{C}$ $T_{VJ} = 25^{\circ}\text{C}$		1.5 1.8	V	
V <sub>TO</sub>	For power-loss calculations only $T_{VJ} = T_{VJM}$		1.13 4.7	V mΩ	
$\mathbf{R}_{thJC}$ $\mathbf{R}_{thCH}$	(version A)	0.25	0.75	K/W K/W	
t <sub>rr</sub>	$I_F = 1 \text{ A}$ ; -di/dt = 200 A/ $\mu$ s; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^{\circ}\text{C}$		50	ns	
I <sub>RM</sub>	$V_R = 350 \text{ V}; I_F = 60 \text{ A}; -di_F/dt = 480 \text{ A}/\mu\text{s}$ $L \le 0.05 \mu\text{H}; T_{VJ} = 100^{\circ}\text{C}$			A	

 $<sup>\</sup>odot$  I<sub>FAVM</sub> rating includes reverse blocking losses at T<sub>VJM</sub>. V<sub>R</sub> =  $0.8 \cdot V_{RRM}$ , duty cycle d = 0.5 Data according to IEC 60747

#### **Features**

- International standard package JEDEC TO-247 AD
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I<sub>RM</sub>-values
- · Soft recovery behaviour
- Epoxy meets UL 94V-0

#### **Applications**

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

### **Advantages**

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- · Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

IXYS reserves the right to change limits, test conditions and dimensions.



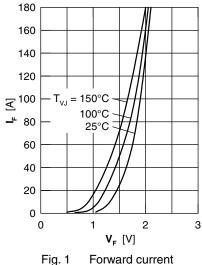


Fig. 1 Forward current versus voltage drop

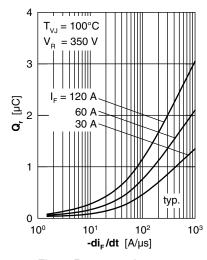


Fig. 2 Recovery charge versus -di<sub>F</sub>/dt

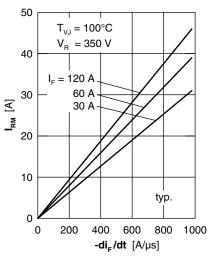


Fig. 3 Peak reverse current versus -di<sub>F</sub>/dt

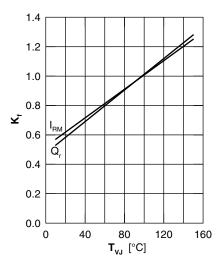


Fig. 4 Dynamic parameters vs. junction temperature

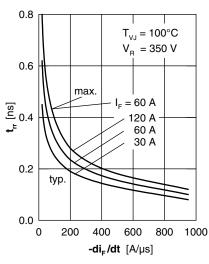


Fig. 5 Recovery time versus -di<sub>F</sub>/dt

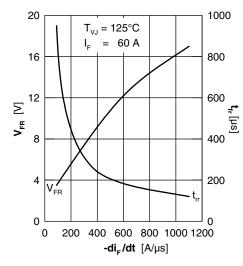


Fig. 6 Peak forward voltage versus di<sub>F</sub>/dt

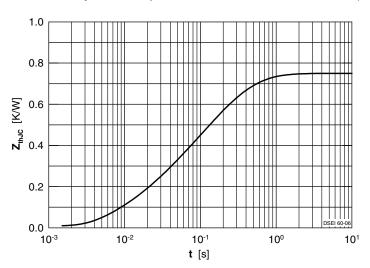
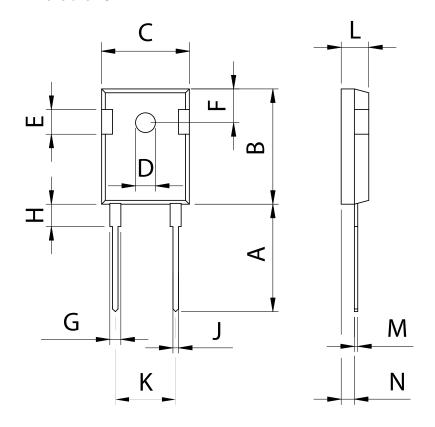


Fig. 7 Transient thermal resistance junction to case



## Dimensions TO-247 AD



Dim.	Millimeter Min. Max.		Inches Min. Max.		
	141111	WIGA.		WIGA.	
A B	19.81 20.80	20.32 21.46	0.780 0.819	0.800 0.845	
С	15.75	16.26	0.610	0.640	
D	3.55	3.65	0.140	0.144	
Е	4.32	5.49	0.170	0.216	
F	5.4	6.2	0.212	0.244	
G	1.65	2.13	0.065	0.084	
Н	-	4.5	-	0.177	
J	1.0	1.4	0.040	0.055	
K	10.8	11.0	0.426	0.433	
L	4.7	5.3	0.185	0.209	
M	0.4	8.0	0.016	0.031	
N	1.5	2.49	0.087	0.102	